

# *sp-d* exchange coupling in Mn doped GaN and ZnO studied by magnetospectroscopy

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# Outline

- Introduction
- Samples and experimental setup
- Results
  - Zero field reflectivity and photoluminescence
  - Magnetoreflectivity spectra and their model description
  - Exchange integral determination: (Ga,Mn)N and (Zn,Mn)O
  - Photoluminescence of (Zn,Mn)O in magnetic field
- Conclusions

p-d exchange integral – chemical trends DMSs based on :

ZnTe, CdTe

- Molecular field approximation  $\checkmark$
- Virtual crystal approximation ✓

## $\beta < 0$

#### CdS

S. Gubarev et al., JETP (1986), M. Nawrocki et al., MRS Proc. (1987). C. Benoit à la Guillaume et al., PRB (1992). J. Tworzydło, PRB (1994); APPA (1995).  Description based on virtual crystal approximation not fully correct



#### GaN, ZnO

(Zn,Co)O: W. Pacuski et al., PRB (2006). (Ga,Mn)N: W. Pacuski et al., PRB (2007). (Ga,Fe)N: W. Pacuski et al., PRL (2008). (Ga,Mn)N: J. Suffczyński et al., PRB (2011). (Zn,Mn)O: W. Pacuski et al., PRB (2011).

- Virtual crystal
- approximation fails
- T. Dietl, PRB (2008).
- C. Śliwa and T. Dietl, PRB (2008).

## **Beyond Virtual Crystal Approximation**



Virtual crystal approximation justified

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#### 

Virtual crystal approximation justified

## **Beyond Virtual Crystal Approximation**





Virtual crystal approximation justified



Strong coupling - virtual crystal approximation does not work

(an analogue of Kondo effect in metals)

T. Dietl, Phys. Rev. B 77, 085208 (2008). C. Śliwa and T. Dietl, Phys. Rev. B 78, 165205 (2008). C. Benoit à la Guillaume et al., Phys. Rev. B 46, 9853 (1992). J. Tworzydło, PRB (1994).; APPA (1995). p-d exchange integral – chemical trends DMSs based on :

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• Virtual crystal approximation fails

 $\beta^{(app)} > 0$  $\beta^{(app)}$  reduced

reduced

T. Dietl, PRB (2008). *α*<sup>(app)</sup>
C. Śliwa and T. Dietl, PRB (2008).

p-d exchange integral – chemical trends DMSs based on :

ZnTe, CdTe

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- Virtual crystal approximation ✓

 $\beta < 0$ 

reduced

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• Virtual crystal approximation fails

T. Dietl, PRB (2008). *O*(*app*)

C. Śliwa and T. Dietl, PRB (2008).

# Samples

## (Ga,Mn)N

(Ga,Mn)N (<700 nm)	↑c - axis
GaN (1300 nm)	
Sapphire	

 $x_{Mn}$  < 0.9 % (SQUID and SIMS)

MOVPE grown (one series)

(Zn,Mn)O



x<sub>Mn</sub> < 3 % (SIMS)

MOCVD or MBE grown



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J. Kepler University, Linz, Austria

## Zero field spectroscopy



- Well resolved excitonic transitions in reflectivity
- Excitons shift towards higher energies with increasing Mn content

# Band gap energy vs Mn concentration



 → Increase of the band gap with increasing Mn concentration: (contrary to e. g. ZnMnSe case)
 in agreement with the recent theoretical predictions

## Reflectivity in magnetic field – (Ga, Mn)N



- Reflectivity in magnetic field confirms identification of excitonic transitions
- Well resolved excitonic shifts

#### Model of the Reflectivity spectra

Dielectric function for GaN and (Ga,Mn)N layers:  

$$\varepsilon_{j}(E) = \varepsilon_{0} + \frac{4\pi \cdot \alpha_{Aj} \cdot E_{Aj}^{2}}{(E_{Aj} - E)^{2} - i \cdot E \cdot \Gamma_{Aj}} + \frac{4\pi \cdot \alpha_{Bj} \cdot E_{Bj}^{2}}{(E_{Bj} - E)^{2} - i \cdot E \cdot \Gamma_{Bj}} + \frac{4\pi \cdot \alpha_{Cj} \cdot E_{Cj}^{2}}{(E_{Cj} - E)^{2} - i \cdot E \cdot \Gamma_{Cj}} + \frac{4\pi \cdot \alpha_{Cj} \cdot E_{Cj}^{2}}{(E_{Cj} - E)^{2} - i \cdot E \cdot \Gamma_{Cj}} + \frac{4\pi \cdot \alpha_{Cj} \cdot E_{Cj}^{2}}{(E_{Cj} - E)^{2} - i \cdot E \cdot \Gamma_{Cj}} + \frac{4\pi \cdot \alpha_{Cj} \cdot E_{Cj}^{2}}{(E_{Cj} - E)^{2} - i \cdot E \cdot \Gamma_{Cj}} + \frac{4\pi \cdot \alpha_{Cj} \cdot E_{Cj}^{2}}{(E_{Cj} - E)^{2} - i \cdot E \cdot \Gamma_{Cj}} + \frac{4\pi \cdot \alpha_{Cj} \cdot E_{Cj}^{2}}{(E_{Cj} - E)^{2} - i \cdot E \cdot \Gamma_{Cj}} + \frac{4\pi \cdot \alpha_{Cj} \cdot E_{Cj}^{2}}{(E_{Cj} - E)^{2} - i \cdot E \cdot \Gamma_{Cj}} + \frac{4\pi \cdot \alpha_{Cj} \cdot E_{Cj}^{2}}{(E_{Cj} - E)^{2} - i \cdot E \cdot \Gamma_{Cj}} + \frac{4\pi \cdot \alpha_{Cj} \cdot E_{Cj}^{2}}{(E_{Cj} - E)^{2} - i \cdot E \cdot \Gamma_{Cj}} + \frac{4\pi \cdot \alpha_{Cj} \cdot E_{Cj}^{2}}{(E_{Cj} - E)^{2} - i \cdot E \cdot \Gamma_{Cj}} + \frac{4\pi \cdot \alpha_{Cj} \cdot E_{Cj}^{2}}{(E_{Cj} - E)^{2} - i \cdot E \cdot \Gamma_{Cj}} + \frac{4\pi \cdot \alpha_{Cj} \cdot E_{Cj}^{2}}{(E_{Cj} - E)^{2} - i \cdot E \cdot \Gamma_{Cj}} + \frac{4\pi \cdot \alpha_{Cj} \cdot E_{Cj}^{2}}{(E_{Cj} - E)^{2} - i \cdot E \cdot \Gamma_{Cj}} + \frac{4\pi \cdot \alpha_{Cj} \cdot E_{Cj}^{2}}{(E_{Cj} - E)^{2} - i \cdot E \cdot \Gamma_{Cj}} + \frac{4\pi \cdot \alpha_{Cj} \cdot E_{Cj}^{2}}{(E_{Cj} - E)^{2} - i \cdot E \cdot \Gamma_{Cj}} + \frac{4\pi \cdot \alpha_{Cj} \cdot E_{Cj}^{2}}{(E_{Cj} - E)^{2} - i \cdot E \cdot \Gamma_{Cj}} + \frac{4\pi \cdot \alpha_{Cj} \cdot E_{Cj}^{2}}{(E_{Cj} - E)^{2} - i \cdot E \cdot \Gamma_{Cj}} + \frac{4\pi \cdot \alpha_{Cj} \cdot E_{Cj}^{2}}{(E_{Cj} - E)^{2} - i \cdot E \cdot \Gamma_{Cj}} + \frac{4\pi \cdot \alpha_{Cj} \cdot E_{Cj}^{2}}{(E_{Cj} - E)^{2} - i \cdot E \cdot \Gamma_{Cj}} + \frac{4\pi \cdot \alpha_{Cj} \cdot E_{Cj}^{2}}{(E_{Cj} - E)^{2} - i \cdot E \cdot \Gamma_{Cj}} + \frac{4\pi \cdot \alpha_{Cj} \cdot E_{Cj}^{2}}{(E_{Cj} - E)^{2} - i \cdot E \cdot \Gamma_{Cj}} + \frac{4\pi \cdot \alpha_{Cj} \cdot E_{Cj}^{2}}{(E_{Cj} - E)^{2} - i \cdot E \cdot \Gamma_{Cj}} + \frac{4\pi \cdot \alpha_{Cj} \cdot E_{Cj}^{2}}{(E_{Cj} - E)^{2} - i \cdot E \cdot \Gamma_{Cj}} + \frac{4\pi \cdot \alpha_{Cj} \cdot E_{Cj}^{2}}{(E_{Cj} - E)^{2} - i \cdot E \cdot \Gamma_{Cj}} + \frac{4\pi \cdot \alpha_{Cj} \cdot E_{Cj}^{2}}{(E_{Cj} - E)^{2} - i \cdot E \cdot \Gamma_{Cj}} + \frac{4\pi \cdot \alpha_{Cj} \cdot E_{Cj}^{2}}{(E_{Cj} - E)^{2} - i \cdot E \cdot \Gamma_{Cj}} + \frac{4\pi \cdot \alpha_{Cj} \cdot E_{Cj}^{2}}{(E_{Cj} - E)^{2} - i \cdot E \cdot \Gamma_{Cj}} + \frac{4\pi \cdot \alpha_{Cj} \cdot E_{Cj}^{2}}{(E_{Cj} - E)^{2} - i \cdot E \cdot \Gamma_{Cj}} + \frac{4\pi \cdot \alpha_{Cj} \cdot E_{Cj}^{2$$

+ *excitonic excited states* + *continuum of unbound states* 

Fitting parameters: energies, widths and polarizabilites of excitons A, B, C:



## Reflectivity in magnetic field – (Zn,Mn)O



- Clear observation of the giant Zeeman splitting of 1S and 2S excitons
- Correct model description

# Modelling of the of the excitonic shifts in magnetic field

Effective Hamiltonian:

$$H = E_0 + H_V + H_{e-h} + H_{s,p-d} + H_{Zeeman} + H_{dia}$$

Hamiltonian of exchange interaction between Mn<sup>3+</sup> ions and free carriers:

$$H_{s,p-d}^{\sigma\pm} = \pm \frac{1}{2} N_0 x_{Mn} \langle -S_Z \rangle \begin{pmatrix} \beta - \alpha & 0 & 0 \\ 0 & \alpha - \beta & 0 \\ 0 & 0 & \alpha + \beta \end{pmatrix}$$

 $\rightarrow$  Free parameters of the fit: N<sub>0</sub> $\alpha$ , N<sub>0</sub> $\beta$ , band gap energy, splittings  $\Delta_1, \Delta_2$ 

## Excitonic splitting in magnetic field

(Ga,Mn)N

(Zn,Mn)O



- Quantitative description of excitonic shifts in magnetic field
- Anticrossing of A and B excitons due to e-h exchange interaction
- Magnitude of A and B exciton splittings:

 $\rightarrow$  exciton A in (Zn,Mn)O has r<sub>7</sub> symmetry

#### Exchange constants



• Apparent  $N_0 \alpha^{(app)}$  in (Ga,Mn)N - small

as expected from the recent theories

#### Exchange constants



#### Photoluminescence in magnetic field – (Zn,Mn)O



- No e-h exchange  $\rightarrow$  no exciton anticrossing
- $\Gamma_9$  shift larger than  $\Gamma_7$  shift

## Conclusions

- Band gap of (Ga,Mn)N and (Zn,Mn)O increases with Mn concentration
- Apparent p-d exchange energies  $N_0\beta$  much reduced and ferromagnetic:  $N_0\beta^{(app)} = +0.8 \pm 0.2$  for (Ga,Mn)N and + 0.5 ± 0.15 eV for (Zn,Mn)O
- Apparent s-d exchange energy in (Ga,Mn)N small:  $N_0 a^{(app)} = +0.0 \pm 0.1 \text{ eV}$
- Opposite circular polarization of reflectivity in ZnO as compared to GaN due to reversed valence band ordering
   → Recent models /T. Dietl, PRB (2008).; C. Śliwa and T. Dietl, PRB (2008)./ of wide gap DMSs confirmed
- Mutually opposite polarization of excitonic photoluminescence and reflectivity from (Zn,Mn)O explained

# Strong coupling regime



Dietl, PRB'08